



CMOS Static RAM 256K (32K x 8-Bit)

IDT71256SA/TTSA

Features

- ◆ 32K x 8 advanced high-speed CMOS static RAM
- ◆ Commercial (0° to 70°C) and Industrial (-40° to 85°C) temperature options
- ◆ Equal access and cycle times
 - Commercial and Industrial: 12/15/20/25ns
- ◆ One Chip Select plus one Output Enable pin
- ◆ Bidirectional data inputs and outputs directly TTL-compatible
- ◆ Low power consumption via chip deselect
- ◆ Commercial product available in 28-pin 300- and 600-mil Plastic DIP, 300 mil Plastic SOJ and TSOP packages
- ◆ Industrial product available in 28-pin 300 mil Plastic SOJ and TSOP packages

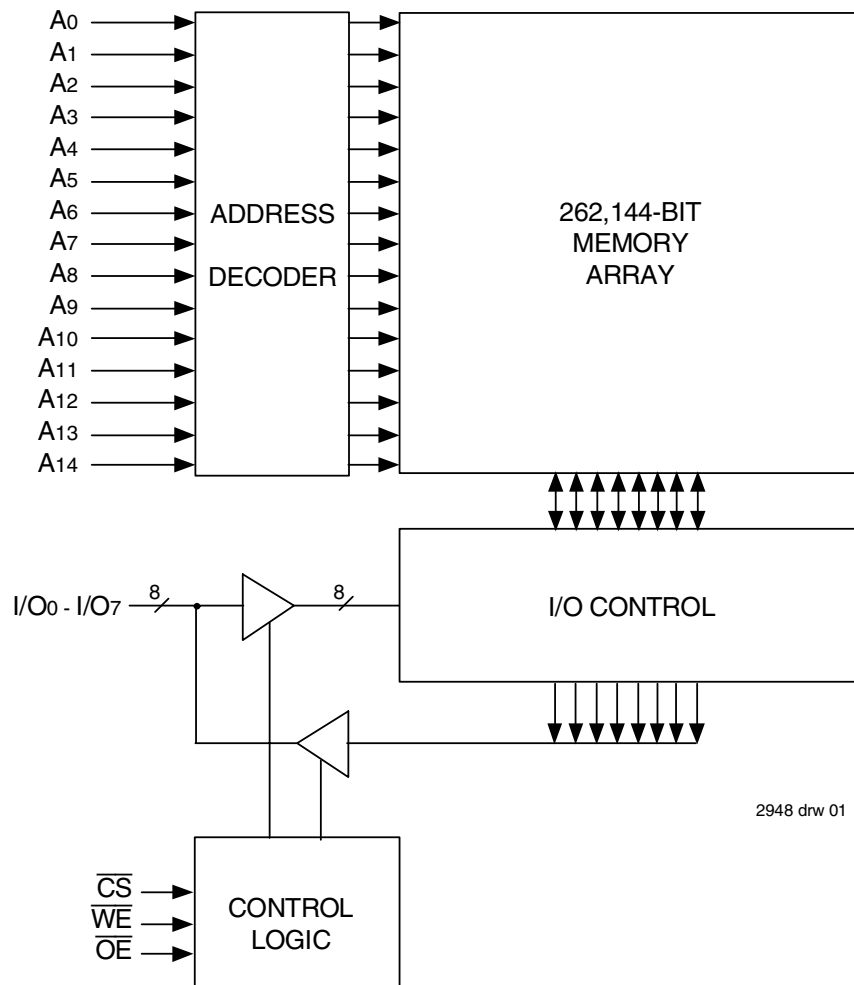
Description

The IDT71256SA is a 262,144-bit high-speed Static RAM organized as 32K x 8. It is fabricated using IDT's high-performance, high-reliability CMOS technology. This state-of-the-art technology, combined with innovative circuit design techniques, provides a cost-effective solution for high-speed memory needs.

The IDT71256SA has an output enable pin which operates as fast as 6ns, with address access times as fast as 12ns. All bidirectional inputs and outputs of the IDT71256SA are TTL-compatible and operation is from a single 5V supply. Fully static asynchronous circuitry is used, requiring no clocks or refresh for operation.

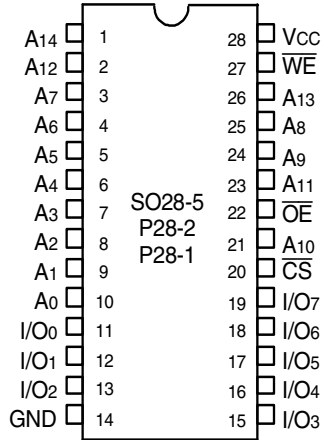
The IDT71256SA is packaged in 28-pin 300- and 600-mil Plastic DIP, 28-pin 300 mil Plastic SOJ and TSOP.

Functional Block Diagram



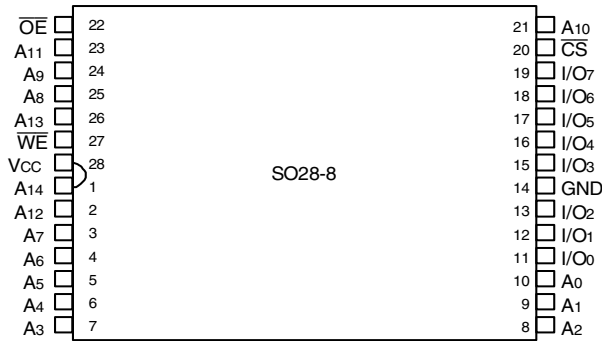
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Pin Configurations



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DIP/SOJ
Top View



2948 drw 02a

TSOP
Top View

Absolute Maximum Ratings⁽¹⁾

Symbol	Rating	Value	Unit
V _{CC}	Supply Voltage Relative to GND	-0.5 to +7.0	V
V _{TERM}	Terminal Voltage Relative to GND	-0.5 to V _{CC} +0.5	V
T _{BIAS}	Temperature Under Bias	-55 to +125	°C
T _{STG}	Storage Temperature	-55 to +125	°C
P _T	Power Dissipation	1.0	W
I _{OUT}	DC Output Current	50	mA

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NOTE:

- Stresses greater than those listed under ABSOLUTE MAXIMUM RATINGS may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect reliability.

Truth Table^(1,2)

\overline{CS}	\overline{OE}	\overline{WE}	I/O	Function
L	L	H	DATA _{OUT}	Read Data
L	X	L	DATA _{IN}	Write Data
L	H	H	High-Z	Outputs Disabled
H	X	X	High-Z	Deselected - Standby (I _S B)
V _{Hc} ⁽³⁾	X	X	High-Z	Deselected - Standby (I _S B1)

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NOTES:

- H = V_{IH}, L = V_{IL}, x = Don't care.
- V_{LC} = 0.2V, V_{Hc} = V_{CC} - 0.2V.
- Other inputs ≥ V_{Hc} or ≤ V_{LC}.

Recommended Operating Temperature and Supply Voltage

Grade	Temperature	GND	V _{CC}
Commercial	0°C to +70°C	0V	4.5V ± 5.5V
Industrial	-40°C to +85°C	0V	4.5V ± 5.5V

2948 tbl 01

Recommended DC Operating Conditions

Symbol	Parameter	Min.	Typ.	Max.	Unit
V _{CC}	Supply Voltage	4.5	5.0	5.5	V
GND	Ground	0	0	0	V
V _{IH}	Input High Voltage	2.2	—	V _{CC} + 0.5	V
V _{IL}	Input Low Voltage	-0.5 ⁽¹⁾	—	0.8	V

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NOTE:

- V_{IL} (min.) = -1.5V for pulse width less than 10ns, once per cycle.

DC Electrical Characteristics

($V_{CC} = 5.0V \pm 10\%$)

Symbol	Parameter	Test Conditions	IDT71256SA		Unit
			Min.	Max.	
$ I_{LI} $	Input Leakage Current	$V_{CC} = \text{Max.}, V_{IN} = \text{GND to } V_{CC}$	—	5	μA
$ I_{LO} $	Output Leakage Current	$V_{CC} = \text{Max.}, \overline{CS} = V_{IH}, V_{OUT} = \text{GND to } V_{CC}$	—	5	μA
V_{OL}	Output Low Voltage	$I_{OL} = 8\text{mA}, V_{CC} = \text{Min.}$	—	0.4	V
V_{OH}	Output High Voltage	$I_{OH} = -4\text{mA}, V_{CC} = \text{Min.}$	2.4	—	V

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DC Electrical Characteristics⁽¹⁾

($V_{CC} = 5.0V \pm 10\%$, $V_{LC} = 0.2V$, $V_{HC} = V_{CC} - 0.2V$)

Symbol	Parameter	71256SA12	71256SA15	71256SA20	71256SA25	Unit
I_{CC}	Dynamic Operating Current $CS \leq V_{IL}$, Outputs Open, $V_{CC} = \text{Max.}$, $f = f_{MAX}^{(2)}$	160	150	145	145	mA
I_{SB}	Standby Power Supply Current (TTL Level) $CS \geq V_{IH}$, Outputs Open, $V_{CC} = \text{Max.}$, $f = f_{MAX}^{(2)}$	50	40	40	40	mA
I_{SB1}	Standby Power Supply Current (CMOS Level) $CS \geq V_{HC}$, Outputs Open, $V_{CC} = \text{Max.}$, $f = 0^{(2)}$, $V_{IN} \leq V_{LC}$ or $V_{IN} \geq V_{HC}$	15	15	15	15	mA

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NOTES:

1. All values are maximum guaranteed values.
2. $f_{MAX} = 1/Trc$ (all address inputs are cycling at f_{MAX}); $f = 0$ means no address input lines are changing.

AC Test Conditions

Input Pulse Levels	GND to 3.0V
Input Rise/Fall Times	3ns
Input Timing Reference Levels	1.5V
Output Reference Levels	1.5V
AC Test Load	See Figures 1 and 2

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Capacitance

($T_A = +25^\circ\text{C}$, $f = 1.0\text{MHz}$, SOJ package)

Symbol	Parameter ⁽¹⁾	Conditions	Max.	Unit
C_{IN}	Input Capacitance	$V_{IN} = 3\text{dV}$	7	pF
C_{IO}	I/O Capacitance	$V_{OUT} = 3\text{dV}$	7	pF

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NOTE:

1. This parameter is guaranteed by device characterization, but not production tested.

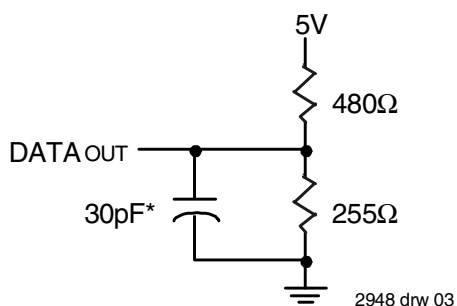


Figure 1. AC Test Load

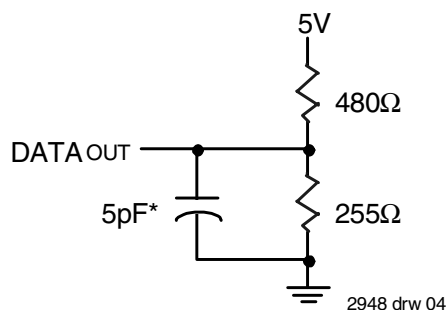


Figure 2. AC Test Load
(for tCLZ, tOLZ, tCHZ, tOHZ, tOW, and tWHZ)

*Including jig and scope capacitance.

AC Electrical Characteristics ($V_{CC} = 5.0V \pm 10\%$)

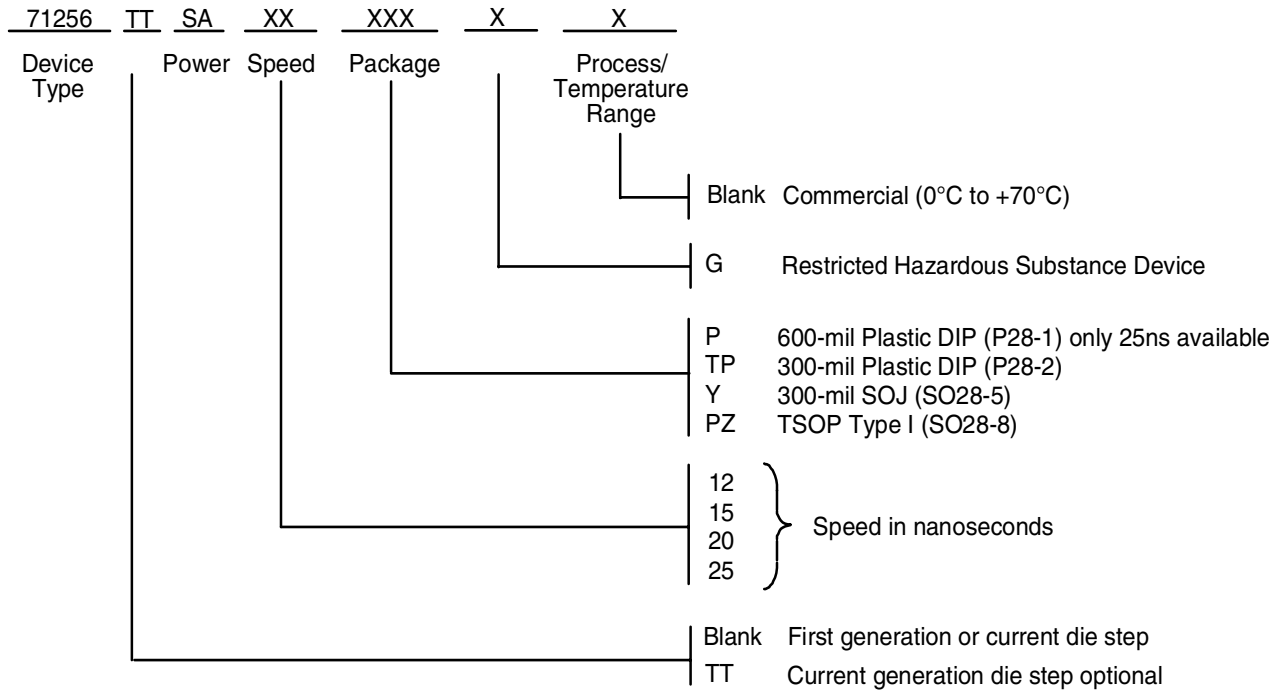
Symbol	Parameter	71256SA12		71256SA15		71256SA20		71256SA25		Unit
		Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	
Read Cycle										
t _{RC}	Read Cycle Time	12	—	15	—	20	—	25	—	ns
t _{AA}	Address Access Time	—	12	—	15	—	20	—	25	ns
t _{ACS}	Chip Select Access Time	—	12	—	15	—	20	—	25	ns
t _{CLZ} ⁽¹⁾	Chip Select to Output in Low-Z	4	—	4	—	4	—	4	—	ns
t _{CHZ} ⁽¹⁾	Chip Select to Output in High-Z	0	6	0	7	0	10	0	11	ns
t _{OE}	Output Enable to Output Valid	—	6	—	7	—	10	—	11	ns
t _{OLZ} ⁽¹⁾	Output Enable to Output in Low-Z	0	—	0	—	0	—	0	—	ns
t _{OHZ} ⁽¹⁾	Output Disable to Output in High-Z	0	6	0	6	0	8	0	10	ns
t _{OH}	Output Hold from Address Change	3	—	3	—	3	—	3	—	ns
t _{PU} ⁽¹⁾	Chip Select to Power Up Time	0	—	0	—	0	—	0	—	ns
t _{PD} ⁽¹⁾	Chip Deselect to Power Down Time	—	12	—	15	—	20	—	25	ns
Write Cycle										
t _{WC}	Write Cycle Time	12	—	15	—	20	—	25	—	ns
t _{AW}	Address Valid to End-of-Write	9	—	10	—	15	—	20	—	ns
t _{CW}	Chip Select to End-of-Write	9	—	10	—	15	—	20	—	ns
t _{AS}	Address Set-up Time	0	—	0	—	0	—	0	—	ns
t _{WP}	Write Pulse Width	8	—	10	—	15	—	20	—	ns
t _{WR}	Write Recovery Time	0	—	0	—	0	—	0	—	ns
t _{DW}	Data Valid to End-of-Write	6	—	7	—	11	—	13	—	ns
t _{DH}	Data Hold Time	0	—	0	—	0	—	0	—	ns
t _{OW} ⁽¹⁾	Output Active from End-of-Write	4	—	4	—	4	—	4	—	ns
t _{WHZ} ⁽¹⁾	Write Enable to Output in High-Z	0	6	0	6	0	10	0	11	ns

2948 tbl 09

NOTE:

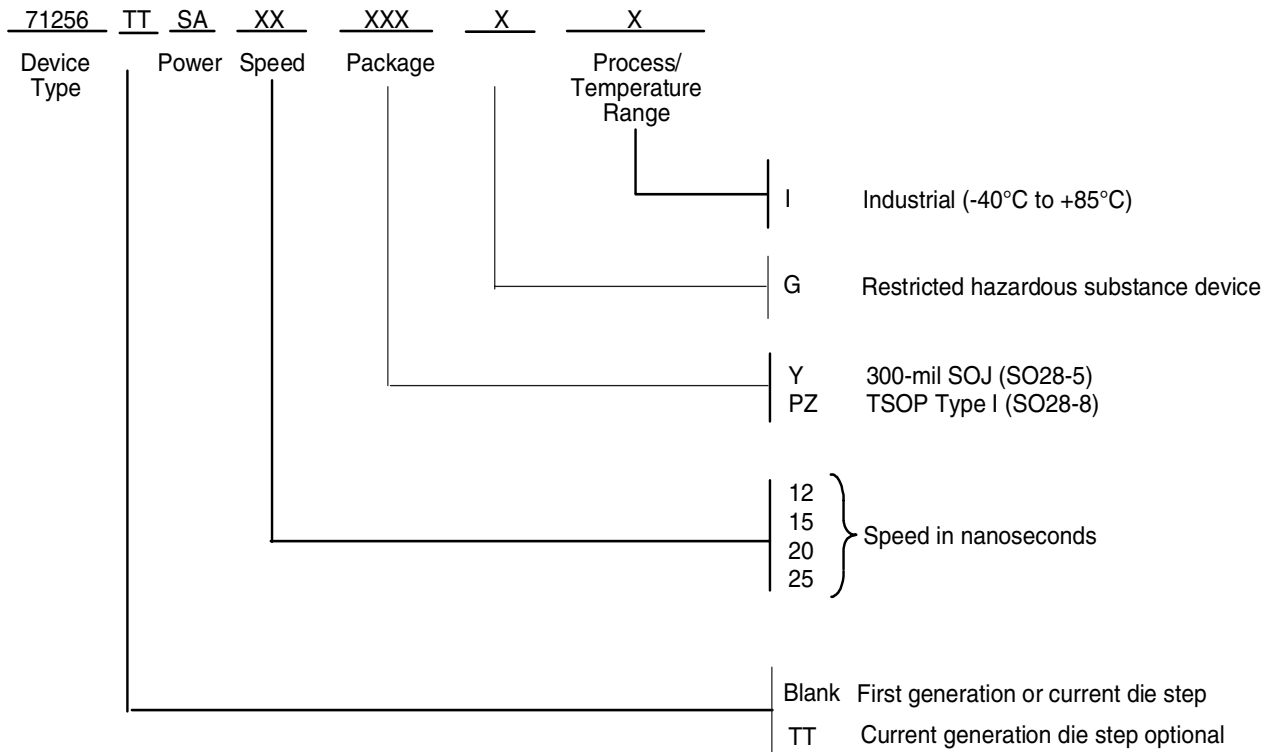
1. This parameter is guaranteed with the AC Load (Figure 2) by device characterization, but is not production tested.

Ordering Information — Commercial



Ordering Information — Industrial

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2948 drw 10